

B08-XX00
Bi-DIRECTIONAL
THYRISTOR

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (°C)	VALUE			UNIT
				Min	Type	Max	
I _{T(RMS)}	RMS current	50Hz sine wave Double side cooled, T _{HS} =55°C	125			1160	A
I _{T(RMS)}	RMS current	50Hz sine wave Double side cooled, T _{HS} =80°C	125			862	A
V _{RRM}	Repetitive peak reverse voltage	V _{RRM} tp=10ms V _{RSM} = V _{DRM} &V _{RRM} +100V	125	500		1800	V
I _{RRM}	Repetitive peak current	at V _{RRM}	125			50	mA
I _{TSM}	Surge on-state current	10ms half sine wave	125			6.8	KA
I ² T	I ² T for fusing coordination	V _R =0.6V _{RRM}				231	A ² s*10 ⁻³
V _{TO}	Threshold voltage		125			1.0	V
r _T	On-state slop resistance					0.85	mΩ
V _{TM}	Peak on-state voltage	I _{TM} =1200A, F=18KN	125			2.02	V
dv/dt	Critical rate of rise of off-state voltage	V _{DM} =0.67V _{DRM}	125			50	V/μs
di/dt	Critical rate of rise of on-state current	From 67%V _{DRM} to 1500A, Gate source 1.5A t _r ≤0.5μs Repetitive	125			50	A/μs
I _{GT}	Gate trigger current	V _A =12V, I _A =1A	25	20		350	mA
V _{GT}	Gate trigger voltage			0.8		3.5	V
I _H	Holding current			20		400	mA
R _{th(j-h)}	Thermal resistance Junction to heatsink	At 180° sine double side cooled Clamping force 18KN				0.035	°C /W
F _m	Mounting force			15		20	KN
T _{stg}	Stored temperature			-40		140	°C
W _t	Weight				360		g
Outline	KT39cT40						

Outline

